

Homework 8 Solutions

1. Electromagnetic Power Density [7 Points]

A wave traveling in a non-magnetic medium with $\epsilon_r = 16$ has an electric field:

$$\vec{E} = [2 \cos(\pi 10^6 t + kx) \hat{y} - 3 \cos(\pi 10^6 t + kx) \hat{z}] \text{ [V/m]}$$

- a) Determine the propagation direction of the wave.

propagation direction: $-x$ (+1)

- b) Determine the magnetic field \vec{H} .

$$\vec{H} = \hat{k} \times \frac{\vec{E}}{\eta} \quad \eta = \sqrt{\frac{\mu}{\epsilon}} = \frac{1}{4} \sqrt{\frac{\mu_0}{\epsilon_0}} = \frac{377 \Omega}{4} = 94.25 \Omega$$

$$\vec{H} = (-\hat{x}) \times \frac{[2 \cos(\pi 10^6 t + kx) \hat{y} - 3 \cos(\pi 10^6 t + kx) \hat{z}]}{94.25 \Omega} \text{ A/m}$$

$$= -0.021 \cos(\pi 10^6 t + kx) \hat{z} - 0.032 \cos(\pi 10^6 t + kx) \hat{y} \text{ A/m}$$

(+1) correct magnitudes; (+1) correct propagation direction
(+1) correct H direction vectors

- c) Calculate the average power density of the wave.

$$S_{av} = \frac{1}{2} \text{Re}\{\vec{E} \times \vec{H}^*\} = \frac{1}{2} \frac{|\vec{E}|^2}{\eta} = \frac{1}{2} \left(\frac{2^2 + 3^2}{94.25 \Omega} \right) = 0.069 \text{ [W/m}^2\text{]} \quad (+1)$$

(+1) formula

- d) If we are dealing with a lossy medium, \vec{E} and \vec{H} acquire an extra exponential term $e^{-\alpha z}$. What additional term does the Poynting vector \vec{S} then acquire in a lossy medium?

$$e^{-2\alpha z}, \text{ a factor of } e^{-\alpha z} \text{ from each } \vec{E} \text{ and } \vec{H}$$

since $\vec{S} = \vec{E} \times \vec{H}$ (+1)

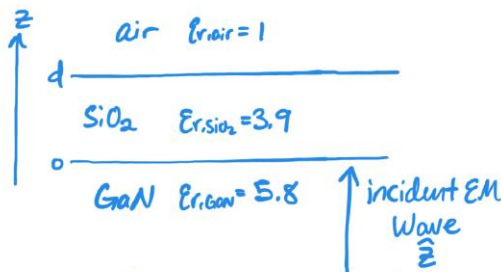
2. Electromagnetic Waves at Material Interfaces (Normal Incidence) [17 Points]

The light from an LED originates from holes and electrons recombining in a semiconductor material and emitting a photon, which then passes through another dielectric material before it is emitted into air. Consider the following system of material interfaces:

- for $z < 0$ the material is GaN with $\epsilon_{r,GaN} = 5.8$
- for $0 < z < d$, the material is SiO₂ with $\epsilon_{r,SiO_2} = 3.9$
- for $d < z < \infty$, the material is air

An electromagnetic wave with $\tilde{E}(r) = 2e^{-jk_{GaN}z} \hat{x}$ [V/m] and a wavelength in GaN equal to 450nm is normally incident on the GaN/SiO₂ interface.

- a) Draw a diagram of this system of materials, including axes, material properties and the direction of travel of the wave.



- (+1) regions drawn in correct locations + axes drawn
 (+1) materials + material properties labeled
 (+1) direction of travel of incident wave shown

- b) What is the frequency f of this electromagnetic wave? Also, calculate k in each material. Is the wavelength different in each material?

$$f = \frac{v}{\lambda} = \frac{1}{\lambda \sqrt{\mu \epsilon}} = \frac{3 \times 10^8 \text{ m/s}}{\sqrt{5.8} \cdot 450 \times 10^{-9} \text{ m}} = 276.8 \text{ THz} \quad (+1)$$

$$\cdot \text{ in GaN: } k_{GaN} = \frac{2\pi}{\lambda_{GaN}} = \frac{2\pi}{450 \times 10^{-9} \text{ m}} = 1.40 \times 10^7 \frac{\text{rad}}{\text{m}} \quad (+1)$$

$$\cdot \text{ in SiO}_2: k_{SiO_2} = \frac{2\pi f}{v_{SiO_2}} = 2\pi f \sqrt{\mu \epsilon_{SiO_2}} = \frac{2\pi \sqrt{3.9} f}{c} = 1.14 \times 10^7 \frac{\text{rad}}{\text{m}} \quad (+1)$$

$$\cdot \text{ in air: } k_{air} = \frac{2\pi f}{v_{air}} = \frac{2\pi f}{c} = 5.80 \times 10^6 \frac{\text{rad}}{\text{m}} \quad (+1)$$

- c) Calculate the reflection coefficient Γ and transmission coefficient τ at the GaN/SiO₂ interface and write the phasor expression for wave transmitted from the GaN into the SiO₂ $\tilde{\mathbf{E}}_{T1}$.

$$\begin{aligned}
 \cdot \eta_{\text{GaN}} &= \sqrt{\frac{\mu_0}{\epsilon_{\text{GaN}}}} = \frac{\eta_0}{\sqrt{\epsilon_{\text{rGaN}}}} = \frac{377\Omega}{\sqrt{5.8}} = 156.5\Omega \\
 \cdot \eta_{\text{SiO}_2} &= \frac{377\Omega}{\sqrt{3.9}} = 190.9\Omega \\
 \cdot \eta_{\text{air}} &= 377\Omega \\
 \cdot \Gamma_{\text{GaN/SiO}_2} &= \frac{\eta_{\text{SiO}_2} - \eta_{\text{GaN}}}{\eta_{\text{SiO}_2} + \eta_{\text{GaN}}} = \frac{190.9\Omega - 156.5\Omega}{190.9\Omega + 156.5\Omega} \\
 &= \underline{0.1} \text{ (+1)} \\
 \cdot \tau_{\text{GaN/SiO}_2} &= 1 + \Gamma_{\text{GaN/SiO}_2} = \underline{1.1} \text{ (+1)} \\
 \cdot \tilde{\mathbf{E}}_{T1} &= \tau_{\text{GaN/SiO}_2} |\tilde{\mathbf{E}}| e^{jk_{\text{SiO}_2} z} \hat{\mathbf{x}} \\
 &= 1.1 \cdot 2 \cdot e^{-j \cdot 1.14 \times 10^7 \cdot z} \hat{\mathbf{x}} = \underline{2.2 e^{-j \cdot 1.14 \times 10^7 \cdot z} \hat{\mathbf{x}} \text{ V/m}} \text{ (+1)}
 \end{aligned}$$

- d) Calculate the reflection coefficient Γ and transmission coefficient τ at the SiO₂/air interface and write the phasor expression for the portion of the incident wave $\tilde{\mathbf{E}}_{T1}$ that is transmitted from the SiO₂ into air $\tilde{\mathbf{E}}_{T2}$.

$$\begin{aligned}
 \cdot \Gamma_{\text{SiO}_2/\text{air}} &= \frac{\eta_{\text{air}} - \eta_{\text{SiO}_2}}{\eta_{\text{air}} + \eta_{\text{SiO}_2}} = \frac{377\Omega - 190.9\Omega}{377\Omega + 190.9\Omega} = \underline{0.328} \text{ (+1)} \\
 \cdot \tau_{\text{SiO}_2/\text{air}} &= 1 + \Gamma_{\text{SiO}_2/\text{air}} = \underline{1.328} \text{ (+1)} \\
 \cdot \tilde{\mathbf{E}}_{T2} &= \tau_{\text{SiO}_2/\text{air}} |\tilde{\mathbf{E}}_{T1}| e^{-jk_{\text{air}} z} \hat{\mathbf{x}} \\
 &= \underline{2.92 e^{-j \cdot 5.8 \times 10^6 \cdot z} \hat{\mathbf{x}} \text{ V/m}} \text{ (+1)}
 \end{aligned}$$

- e) Is more power transmitted into air in this case than would be if there were only a GaN/air interface (i.e. no layer of SiO₂ in between GaN and air)? Ignore transmitted wave components from multiple reflections between the interfaces.

• power transmitted with GaN/SiO₂/air : (+1)

$$|S_{av}| = \frac{1}{2} \frac{|E_T|^2}{\eta_0} = \frac{(3.04 \text{ V/m})^2}{2 \cdot 377 \Omega} = 0.123 \text{ [W/m}^2\text{]}$$

• power transmitted in the case of only a GaN/air interface

$$\tau_{GaN/air} = \Gamma_{GaN/air} + 1 = \frac{\eta_{air} - \eta_{GaN}}{\eta_{air} + \eta_{GaN}} + 1 = \frac{377 \Omega - 156.5 \Omega}{377 \Omega + 156.5 \Omega} + 1$$

$$\tilde{E}_T = \tau_{GaN/air} |\tilde{E}| e^{-j k_{air} z} = 1.41$$

$$= 1.41 \cdot 2 e^{-j \cdot 5.8 \times 10^6 \cdot z} \quad (+1) \text{ amplitude of transmitted wave}$$

$$|S_{av}| = \frac{1}{2} \frac{|E_T|^2}{\eta_0} = \frac{(1.41 \text{ V/m})^2}{2 \cdot 377 \Omega} = 0.0026 \text{ [W/m}^2\text{]} \quad (+1)$$

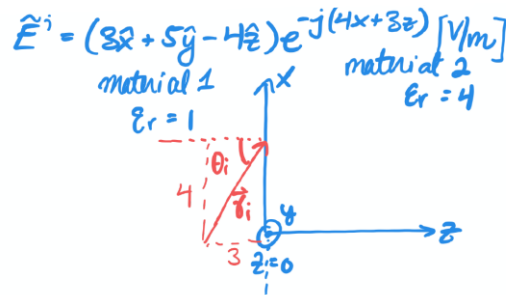
• More power is transmitted by inserting a layer of SiO₂ between the GaN and air.
(+1) conclusion consistent with mathematical findings

3. Electromagnetic Waves at Material Interfaces (Oblique Incidence – Snell's Law)

[12 Points]

A plane wave in air has an electric field defined by $\tilde{\mathbf{E}}^i = (3\hat{x} + 5\hat{y} - 4\hat{z})e^{-j(4x+3z)}$ [V/m] and is incident upon the planar surface of a dielectric material with $\epsilon_r = 4$ that occupies the half-space where $z \geq 0$. Determine:

- a. The angle of incidence (θ_i), angle of refraction (θ_t), and the frequency of the wave.



$$\theta_i = \tan^{-1}(4/3) = 53.1^\circ \quad (+1)$$

$$\begin{aligned} \theta_t: n_i \sin \theta_i &= n_t \sin \theta_t \rightarrow \theta_t = \sin^{-1} \left\{ \frac{n_i}{n_t} \sin \theta_i \right\} \\ &= \sin^{-1} \left\{ \frac{1}{2} \sin(53.1^\circ) \right\} \\ &= 23.6^\circ \quad (+1) \end{aligned}$$

$$\begin{aligned} |\vec{k}| &= \frac{2\pi f n}{c} \rightarrow f = \frac{|\vec{k}|c}{2\pi n} = \frac{\sqrt{4^2 + 3^2}}{2\pi \cdot 1} 3 \times 10^8 \text{ m/s} \\ &= 238.7 \text{ MHz} \quad (+1) \end{aligned}$$

(+1) calculation of $|\vec{k}|$

- b. The reflection and transmission coefficients Γ and τ .

Wave polarization:

$$\begin{aligned} \tilde{\mathbf{E}}^i &= \tilde{\mathbf{E}}_\perp^i + \tilde{\mathbf{E}}_\parallel^i = 5e^{-j(4x+3z)}\hat{y} + (3\hat{x} - 4\hat{z})e^{-j(4x+3z)} \\ &\quad \begin{matrix} \eta_0/2 & \eta_0 & E_\perp & E_\parallel \end{matrix} \\ \Gamma_\perp &= \frac{\eta_2 \cos \theta_i - \eta_1 \cos \theta_t}{\eta_2 \cos \theta_i + \eta_1 \cos \theta_t} = \frac{\frac{\eta_0}{2} \cos(53.1^\circ) - \cos(23.6^\circ)}{\frac{\eta_0}{2} \cos(53.1^\circ) + \cos(23.6^\circ)} \\ &= -0.506 \quad (+1) \end{aligned}$$

$$\tau_\perp = 1 + \Gamma_\perp = 0.494 \quad (+1)$$

$$\Gamma_{11} = \frac{\eta_2 \cos \theta_t - \eta_1 \cos \theta_i}{\eta_2 \cos \theta_t + \eta_1 \cos \theta_i} = \frac{\eta_2 \cos(23.6^\circ) - \cos(53.1^\circ)}{\eta_2 \cos(23.6^\circ) + \cos(53.1^\circ)} = \frac{-1.134}{(+1)}$$

$$\tau_{11} = (1 + \Gamma_{11}) \frac{\cos \theta_i}{\cos \theta_t} = (1 - 0.134) \frac{\cos(53.1^\circ)}{\cos(23.6^\circ)} = \frac{0.506}{(+1)}$$

- c. The field $\tilde{\mathbf{E}}^r$ of the reflected wave, and the field $\tilde{\mathbf{E}}^t$ of the wave transmitted into the dielectric medium.

$$\begin{aligned} \tilde{\mathbf{E}}_r &= \tilde{\mathbf{E}}_{r11} + \tilde{\mathbf{E}}_{r12} = -0.134 \cdot (3\hat{x} + 4\hat{z}) e^{j(4x-3z)} - 0.506 \cdot (5\hat{y}) e^{j(4x-3z)} \\ &= (-0.402\hat{x} - 2.53\hat{y} - 0.636\hat{z}) e^{j(4x-3z)} \quad (+1) \end{aligned}$$

$$|\tilde{\mathbf{r}}_2| = \eta_2 |\tilde{\mathbf{r}}_1| = 2 |\tilde{\mathbf{r}}_1| = 2 \sqrt{4^2 + 3^2} = 10$$

$$r_{2x} = 10 \sin(23.6^\circ) = 4 \quad (+1) \text{ each for } r_{2x}, r_{2z}$$

$$r_{2z} = 10 \cos(23.6^\circ) = 9.16$$

$$\begin{aligned} |E_{11}| &= \sqrt{3^2 + 4^2} = 5; \quad E_{11tx} = 5 \cos(23.6^\circ) = 4.56; \quad E_{11tz} = 5 \sin(23.6^\circ) = 2 \\ \tilde{\mathbf{E}}_t &= \tilde{\mathbf{E}}_{t11} + \tilde{\mathbf{E}}_{t12} = (2.66\hat{x} + 2.47\hat{y} - 1.16\hat{z}) e^{-j(4x+9.16z)} \end{aligned}$$

- d. The average power density carried by the wave into the dielectric medium.

$$S_{av} = \frac{|\tilde{\mathbf{E}}_t|^2}{2\eta_2} = \frac{2.66^2 + 2.47^2 + 1.16^2}{2 \cdot \frac{377}{2}} = \underline{0.038 \text{ W/m}^2}$$

4. Electromagnetic Waves at Material Interfaces (Oblique Incidence – Brewster Angle) [6 Points]

A parallel-polarized plane wave is incident from air onto a (nonmagnetic) dielectric medium with $\epsilon_r = 9$.

- a. What is the Brewster angle for this interface and polarization?

parallel-polarized wave, so

$$\theta_{B||} = \tan^{-1} \left(\sqrt{\frac{\epsilon_2}{\epsilon_1}} \right) = \tan^{-1} \left(\sqrt{\frac{9}{1}} \right) = \underline{71.57^\circ} \quad (+1)$$

(+1): correct equation

- b. If the plane wave is incident on the interface at the Brewster angle, what is the refraction angle?

$$n_i \sin \theta_i = n_t \sin \theta_t \rightarrow \theta_t = \sin^{-1} \left\{ \frac{n_i}{n_t} \sin \theta_i \right\}$$

(+1): correct equation

$$= \sin^{-1} \left\{ \frac{1}{3} \sin (71.57^\circ) \right\}$$

$$= \underline{18.42^\circ} \quad (+1)$$

- c. If the plane wave were perpendicular-polarized instead, what would the Brewster angle be?

Since $\sin \theta_{B\perp} = \sqrt{\frac{1 - (\mu_1 \epsilon_2 / \mu_2 \epsilon_1)}{1 - (\mu_1 / \mu_2)^2}}$ and we have $\mu_1 = \mu_2$ for this system, $\theta_{B\perp}$ is undefined. (+1)

- d. If the plane wave were unpolarized (as light typically is) and incident on the interface at the Brewster angle, what would the polarization of the transmitted wave be?

Since the parallel-polarized component would be completely transmitted and the perpendicular-polarized component would be partially reflected and transmitted, the transmitted wave would have a mixed polarization. (+1)

5. Terms, Notation, Symbols, etc. [8 Points]

On the left-hand side of the table below, write the name of the Greek letter listed in the symbol column and the units that correspond to the symbol. In the right-hand side of the table, write the correct symbol next to the name of the quantity it represents.

Symbol	Name of Greek Letter	Units	Symbol for Quantity	Name of Quantity
α	<i>alpha</i>	<i>Np/m</i>	α	Attenuation Constant
β or k	<i>beta</i>	<i>rad/m</i>	C	Capacitance
γ	<i>gamma</i>	<i>1/m</i>	Z_0	Characteristic Impedance
Γ	<i>gamma</i>	<i>N/A</i>	σ	Conductivity
ϵ_0	<i>epsilon</i>	<i>F/m</i>	\vec{J}_d	Displacement Current Density
\vec{D}	N/A	<i>C/m²</i>	\vec{E}	Electric Field Intensity
\vec{E}	N/A	<i>V/m</i>	V	Electric Scalar Potential
\vec{H}	N/A	<i>A/m</i>	\vec{D}	Electric Flux Density (Displacement Field)
\vec{J}_s	N/A	<i>A/m²</i>	n	Index of Refraction
\vec{J}_d	N/A	<i>A/m²</i>	L	Inductance
ρ_v	<i>rho</i>	<i>C/m³</i>	η	Intrinsic Impedance
λ	<i>lambda</i>	<i>m</i>	\vec{H}	Magnetic Field Intensity
Λ	<i>lambda</i>	<i>Wb</i>	\vec{B}	Magnetic Flux Density
n	N/A	<i>N/A</i>	Λ	Magnetic Flux Linkage
σ	<i>sigma</i>	<i>S/m</i>	\vec{A}	Magnetic Vector Potential
C	N/A	<i>F</i>	ϵ_0	Permeability of Free Space
L	N/A	<i>H</i>	μ_0	Permittivity of Free Space
\mathcal{R}	N/A	<i>H⁻¹</i>	k or β	Phase Constant or Wave Number
\vec{S}_{av}	N/A	<i>W/m²</i>	\vec{S}_{av}	Poynting Vector (avg. power density)
τ	<i>tau</i>	<i>N/A</i>	γ	Propagation Constant
μ_0	<i>mu</i>	<i>H/m</i>	Γ	Reflection Coefficient
V	N/A	<i>V</i>	\mathcal{R}	Reluctance
η	<i>eta</i>	<i>Ω</i>	\vec{J}_s	Surface Current Density
\vec{B}	N/A	<i>Wb/m²</i>	τ	Transmission Coefficient
\vec{A}	N/A	<i>Wb/m</i>	ρ_v	Volume Charge Density
Z_0	N/A	<i>Ω</i>	λ	Wavelength

64 total answers: +8: 64 correct
+7: 56-63 correct
+6: 48-62 correct
+5: 40-47 correct
+4: 32-39 correct
+3: 24-31 correct
+2: 16-23 correct
+1: 8-15 correct
+0: 0-7 correct